

# STB28N65M2, STF28N65M2, STP28N65M2, STW28N65M2

N-channel 650 V, 0.15  $\Omega$  typ., 20 A MDmesh™ M2 Power MOSFETs  
in D<sup>2</sup>PAK, TO-220FP, TO-220 and TO-247 packages

Datasheet - preliminary data

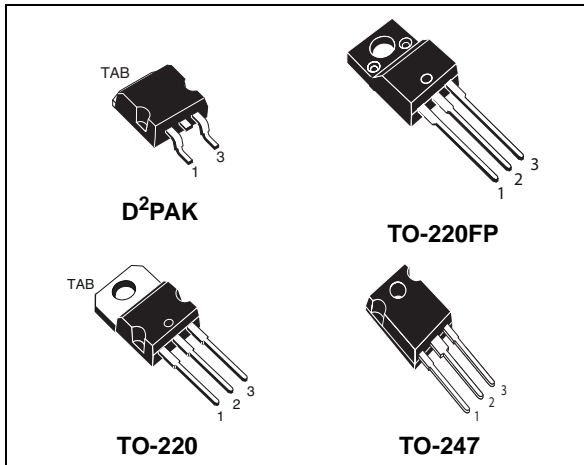
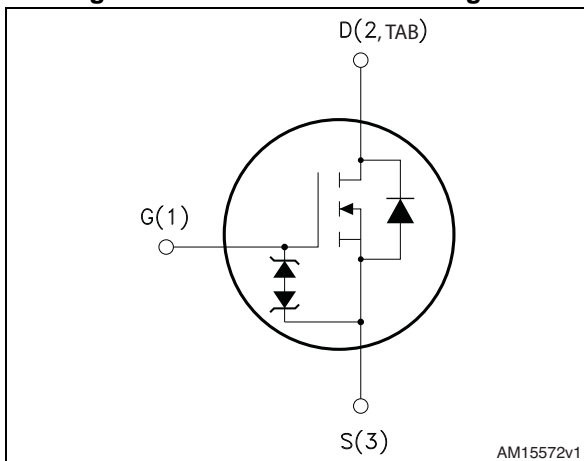


Figure 1. Internal schematic diagram



## Features

Order codes	V <sub>DS</sub>	R <sub>DS(on)</sub> max	I <sub>D</sub>
STB28N65M2	650 V	0.18 $\Omega$	20 A
STF28N65M2			
STP28N65M2			
STW28N65M2			

- Extremely low gate charge
- Excellent output capacitance (C<sub>oss</sub>) profile
- 100% avalanche tested
- Zener-protected

## Applications

- Switching applications

## Description

These devices are N-channel Power MOSFETs developed using MDmesh™ M2 technology. Thanks to their strip layout and improved vertical structure, the devices exhibit low on-resistance and optimized switching characteristics, rendering them suitable for the most demanding high efficiency converters.

Table 1. Device summary

Order codes	Marking	Package	Packaging
STB28N65M2	28N65M2	D <sup>2</sup> PAK	Tape and reel
STF28N65M2		TO-220FP	Tube
STP28N65M2		TO-220	
STW28N65M2		TO-247	

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# 1 Electrical ratings

**Table 2. Absolute maximum ratings**

Symbol	Parameter	Value		Unit
		D <sup>2</sup> PAK, TO-220, TO-247	TO-220FP	
V <sub>GS</sub>	Gate-source voltage	± 25		V
I <sub>D</sub>	Drain current (continuous) at T <sub>C</sub> = 25 °C	20	20 <sup>(1)</sup>	A
I <sub>D</sub>	Drain current (continuous) at T <sub>C</sub> = 100 °C	13	13 <sup>(1)</sup>	A
I <sub>DM</sub> <sup>(2)</sup>	Drain current (pulsed)	80		A
P <sub>TOT</sub>	Total dissipation at T <sub>C</sub> = 25 °C	170	30	W
V <sub>ISO</sub>	Insulation withstand voltage (RMS) from all three leads to external heat sink (t = 1 s; T <sub>C</sub> = 25 °C)		2500	V
dv/dt <sup>(3)</sup>	Peak diode recovery voltage slope	15		V/ns
dv/dt <sup>(4)</sup>	MOSFET dv/dt ruggedness	50		
T <sub>stg</sub>	Storage temperature	- 55 to 150		°C
T <sub>j</sub>	Max. operating junction temperature	150		

1. Current limited by package.
2. Pulse width limited by safe operating area.
3. I<sub>SD</sub> ≤ 20 A, di/dt ≤ 400 A/μs; V<sub>DS peak</sub> < V<sub>(BR)DSS</sub>; V<sub>DD</sub>=520 V
4. V<sub>DS</sub> ≤ 520 V

**Table 3. Thermal data**

Symbol	Parameter	Value				Unit
		D <sup>2</sup> PAK	TO-220FP	TO-220	TO-247	
R <sub>thj-case</sub>	Thermal resistance junction-case max	0.74	4.17	0.74		°C/W
R <sub>thj-pcb</sub> <sup>(1)</sup>	Thermal resistance junction-pcb max	30				°C/W
R <sub>thj-amb</sub>	Thermal resistance junction-ambient max		62.5		50	°C/W

1. When mounted on 1 inch<sup>2</sup> FR-4, 2 Oz copper board

**Table 4. Avalanche characteristics**

Symbol	Parameter	Value	Unit
I <sub>AR</sub>	Avalanche current, repetitive or not repetitive (pulse width limited by T <sub>jmax</sub> )	2.4	A
E <sub>AS</sub>	Single pulse avalanche energy (starting T <sub>j</sub> = 25°C, I <sub>D</sub> = I <sub>AR</sub> ; V <sub>DD</sub> = 50 V)	760	mJ

## 2 Electrical characteristics

( $T_C = 25\text{ °C}$  unless otherwise specified)

**Table 5. On /off states**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$V_{GS} = 0, I_D = 1\text{ mA}$	650			V
$I_{DSS}$	Zero gate voltage drain current	$V_{GS} = 0, V_{DS} = 650\text{ V}$			1	$\mu\text{A}$
		$V_{GS} = 0, V_{DS} = 650\text{ V}$ $T_C = 125\text{ °C}$			100	$\mu\text{A}$
$I_{GSS}$	Gate-body leakage current	$V_{DS} = 0, V_{GS} = \pm 25\text{ V}$			$\pm 10$	$\mu\text{A}$
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	2	3	4	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 10\text{ V}, I_D = 10\text{ A}$		0.15	0.18	$\Omega$

**Table 6. Dynamic**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$C_{iss}$	Input capacitance	$V_{DS} = 100\text{ V}, f = 1\text{ MHz},$ $V_{GS} = 0$	-	1440	-	pF
$C_{oss}$	Output capacitance		-	60	-	pF
$C_{rss}$	Reverse transfer capacitance		-	2	-	pF
$C_{oss\text{ eq}}^{(1)}$	Equivalent output capacitance	$V_{GS} = 0, V_{DS} = 0\text{ to }520\text{ V}$	-	307	-	pF
$R_G$	Intrinsic gate resistance	$f = 1\text{ MHz}$ open drain	-	4.9	-	$\Omega$
$Q_g$	Total gate charge	$V_{DD} = 520\text{ V}, I_D = 20\text{ A},$ $V_{GS} = 10\text{ V}$ (see <a href="#">Figure 19</a> )	-	35	-	nC
$Q_{gs}$	Gate-source charge		-	6	-	nC
$Q_{gd}$	Gate-drain charge		-	15	-	nC

1.  $C_{oss\text{ eq}}$  is defined as a constant equivalent capacitance giving the same charging time as  $C_{oss}$  when  $V_{DS}$  increases from 0 to 80%  $V_{DSS}$

**Table 7. Switching times**

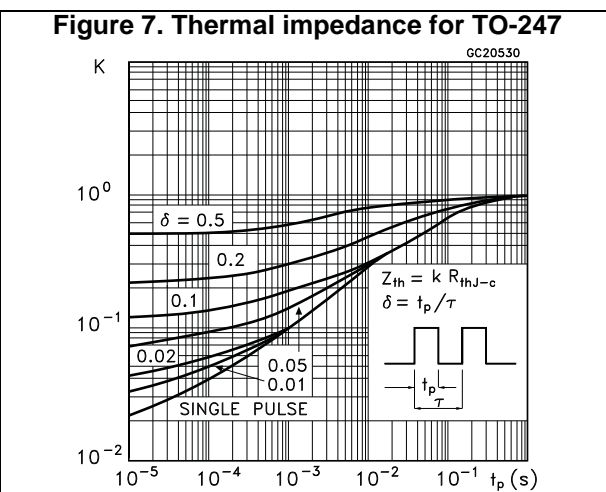
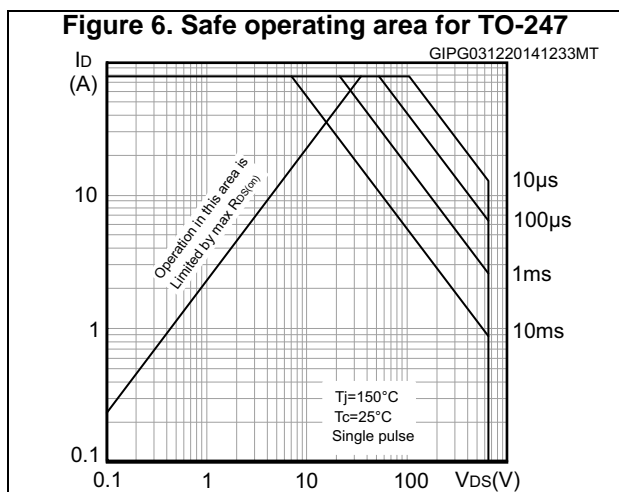
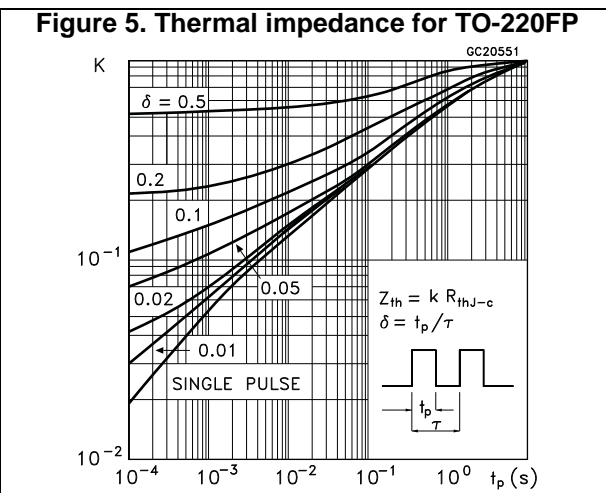
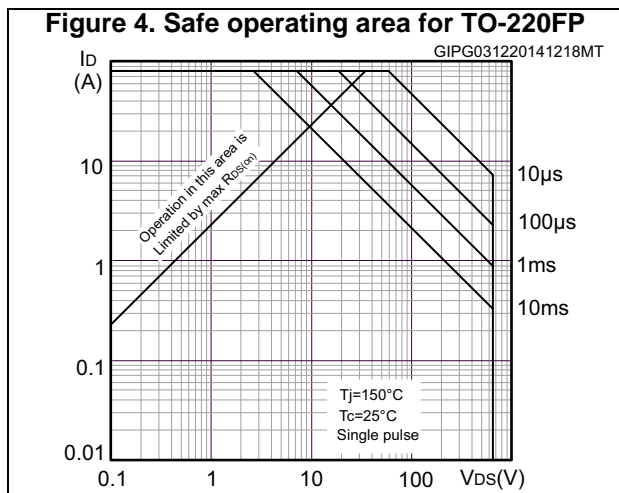
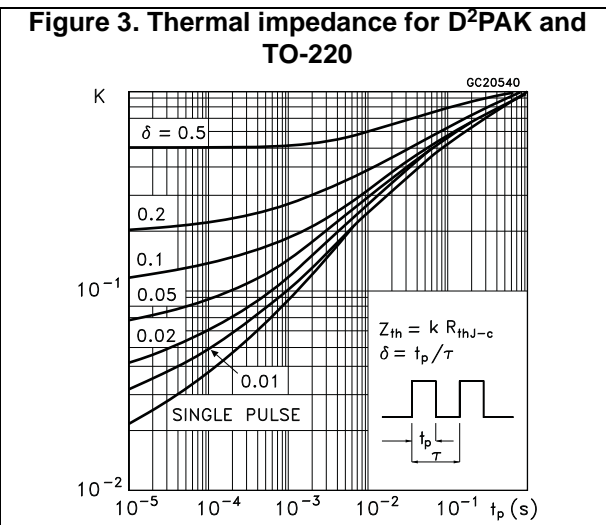
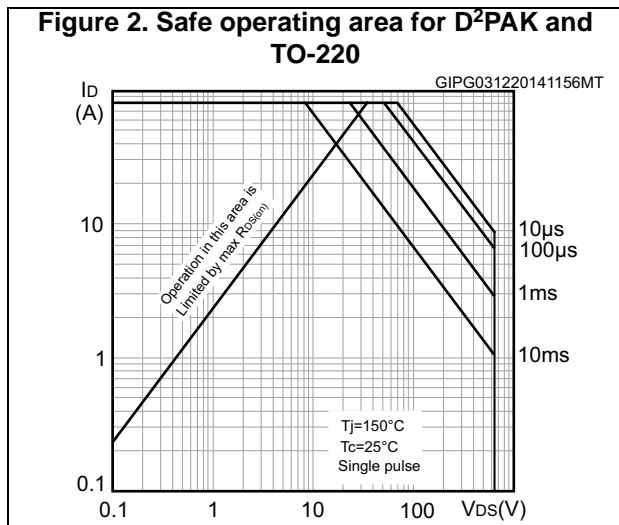
Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 325\text{ V}, I_D = 10\text{ A},$ $R_G = 4.7\text{ }\Omega, V_{GS} = 10\text{ V}$ (see <a href="#">Figure 18</a> and <a href="#">Figure 23</a> )	-	13.4	-	ns
$t_r$	Rise time		-	10	-	ns
$t_{d(off)}$	Turn-off delay time		-	59	-	ns
$t_f$	Fall time		-	8.8	-	ns

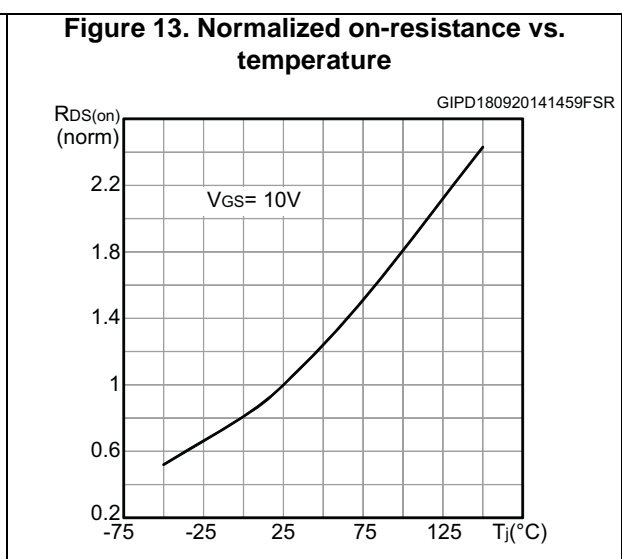
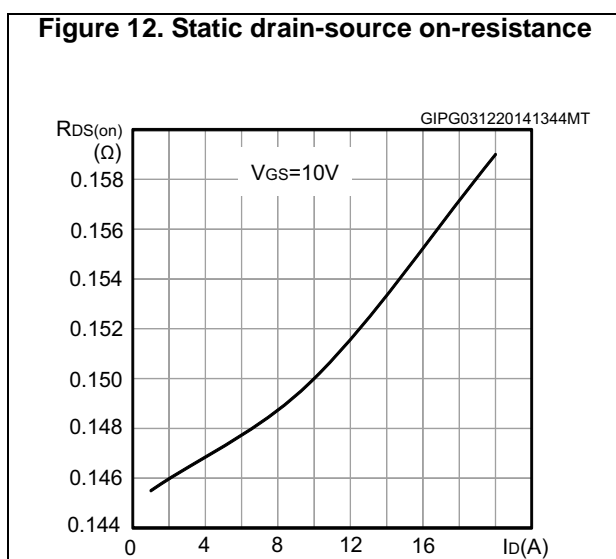
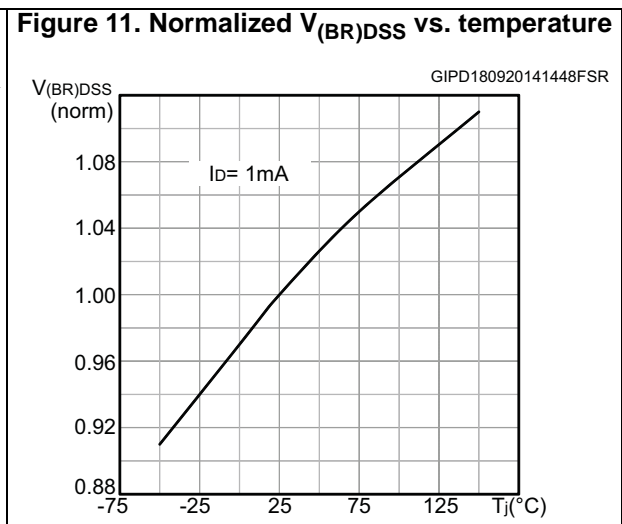
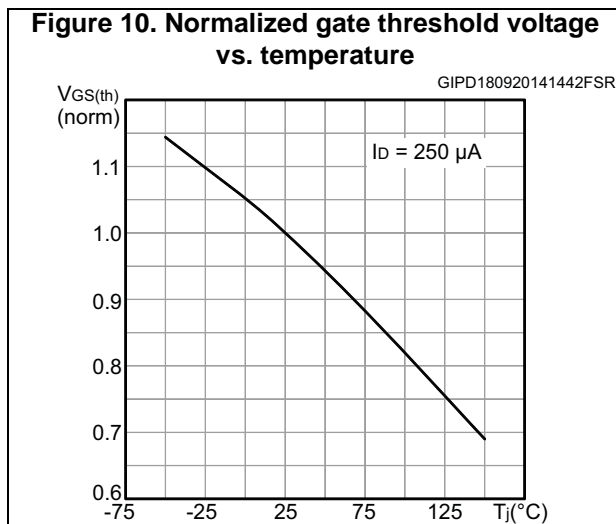
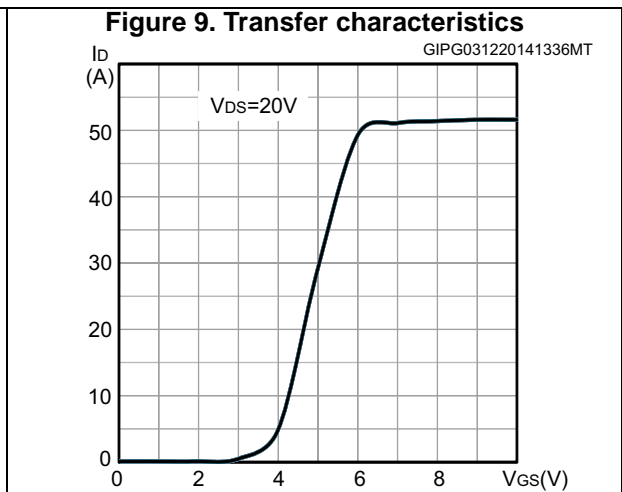
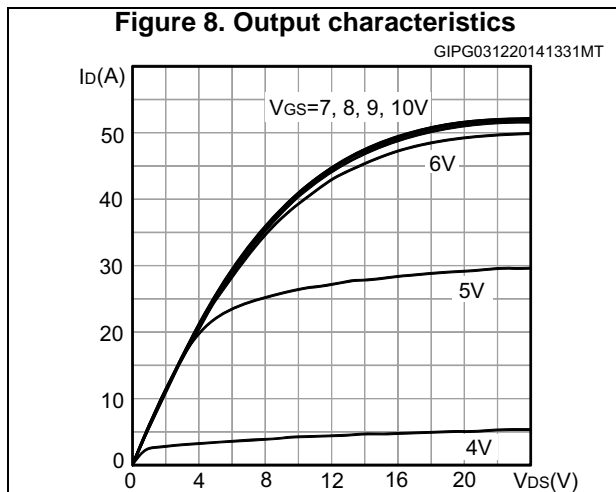
Table 8. Source drain diode

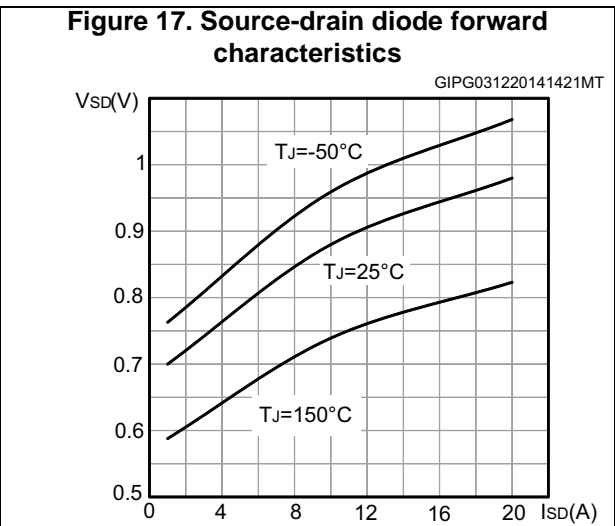
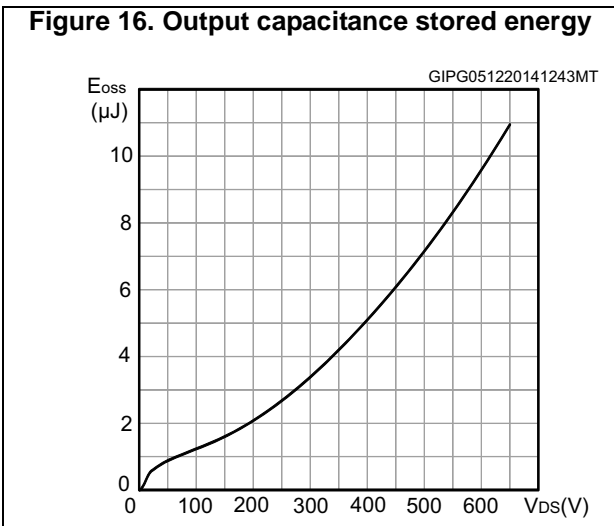
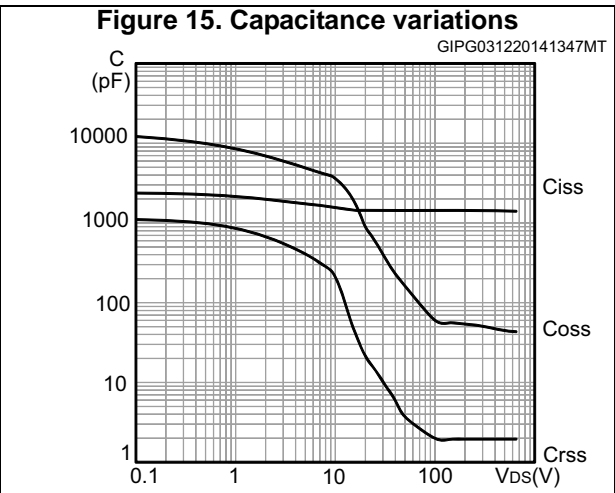
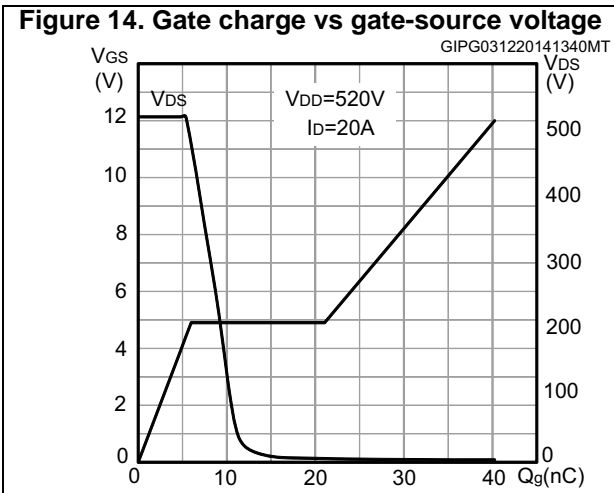
Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_{SD}$	Source-drain current		-		20	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		80	A
$V_{SD}^{(2)}$	Forward on voltage	$V_{GS} = 0, I_{SD} = 20 \text{ A}$	-		1.6	V
$t_{rr}$	Reverse recovery time	$I_{SD} = 20 \text{ A}, di/dt = 100 \text{ A}/\mu\text{s}$ $V_{DD} = 60 \text{ V}$ (see <a href="#">Figure 20</a> )	-	384		ns
$Q_{rr}$	Reverse recovery charge		-	5.7		$\mu\text{C}$
$I_{RRM}$	Reverse recovery current		-	30		A
$t_{rr}$	Reverse recovery time	$I_{SD} = 20 \text{ A}, di/dt = 100 \text{ A}/\mu\text{s}$ $V_{DD} = 60 \text{ V}, T_j = 150 \text{ }^\circ\text{C}$ (see <a href="#">Figure 20</a> )	-	544		ns
$Q_{rr}$	Reverse recovery charge		-	8.2		$\mu\text{C}$
$I_{RRM}$	Reverse recovery current		-	30.5		A

1. Pulse width limited by safe operating area.
2. Pulsed: pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5%

## 2.1 Electrical characteristics (curves)



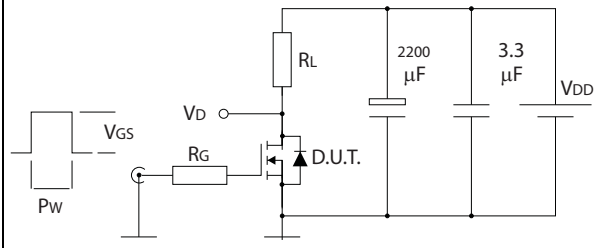






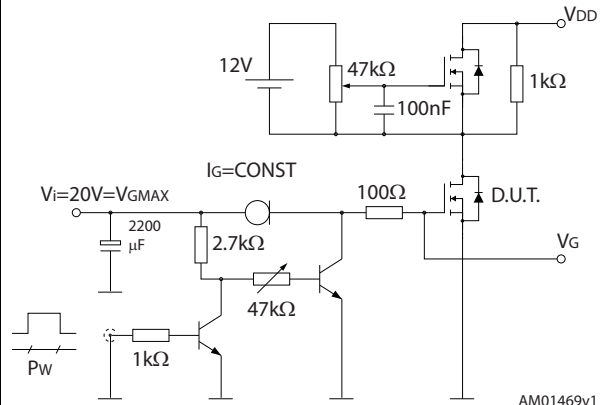
### 3 Test circuits

**Figure 18. Switching times test circuit for resistive load**



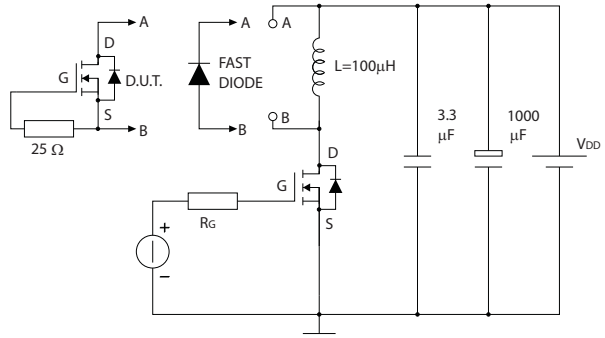
AM01468v1

**Figure 19. Gate charge test circuit**



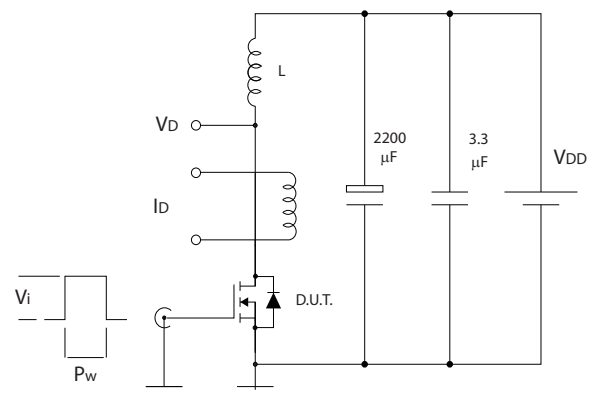
AM01469v1

**Figure 20. Test circuit for inductive load switching and diode recovery times**



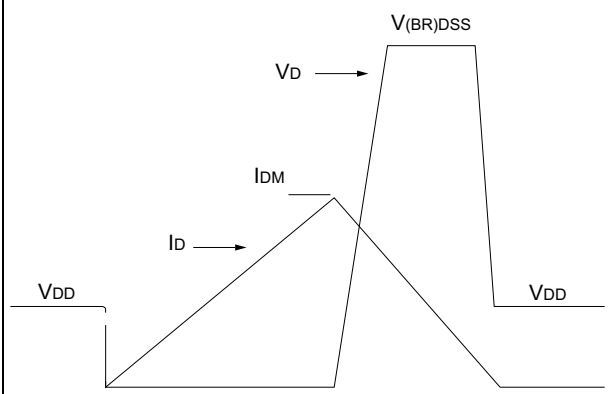
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**Figure 21. Unclamped inductive load test circuit**



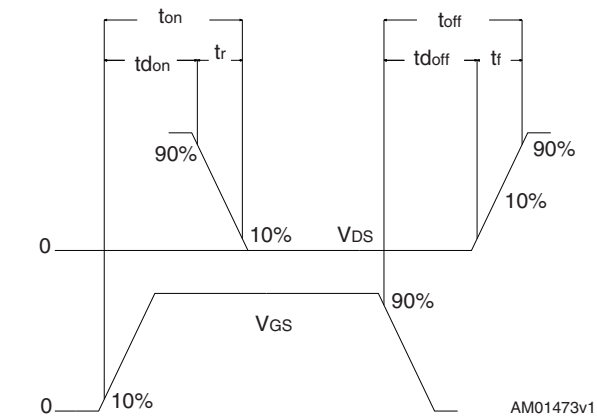
AM01471v1

**Figure 22. Unclamped inductive waveform**



AM01472v1

**Figure 23. Switching time waveform**



AM01473v1

## 4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK<sup>®</sup> packages, depending on their level of environmental compliance. ECOPACK<sup>®</sup> specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK<sup>®</sup> is an ST trademark.

### 4.1 D<sup>2</sup>PAK, STB28N65M2

Figure 24. D<sup>2</sup>PAK drawing

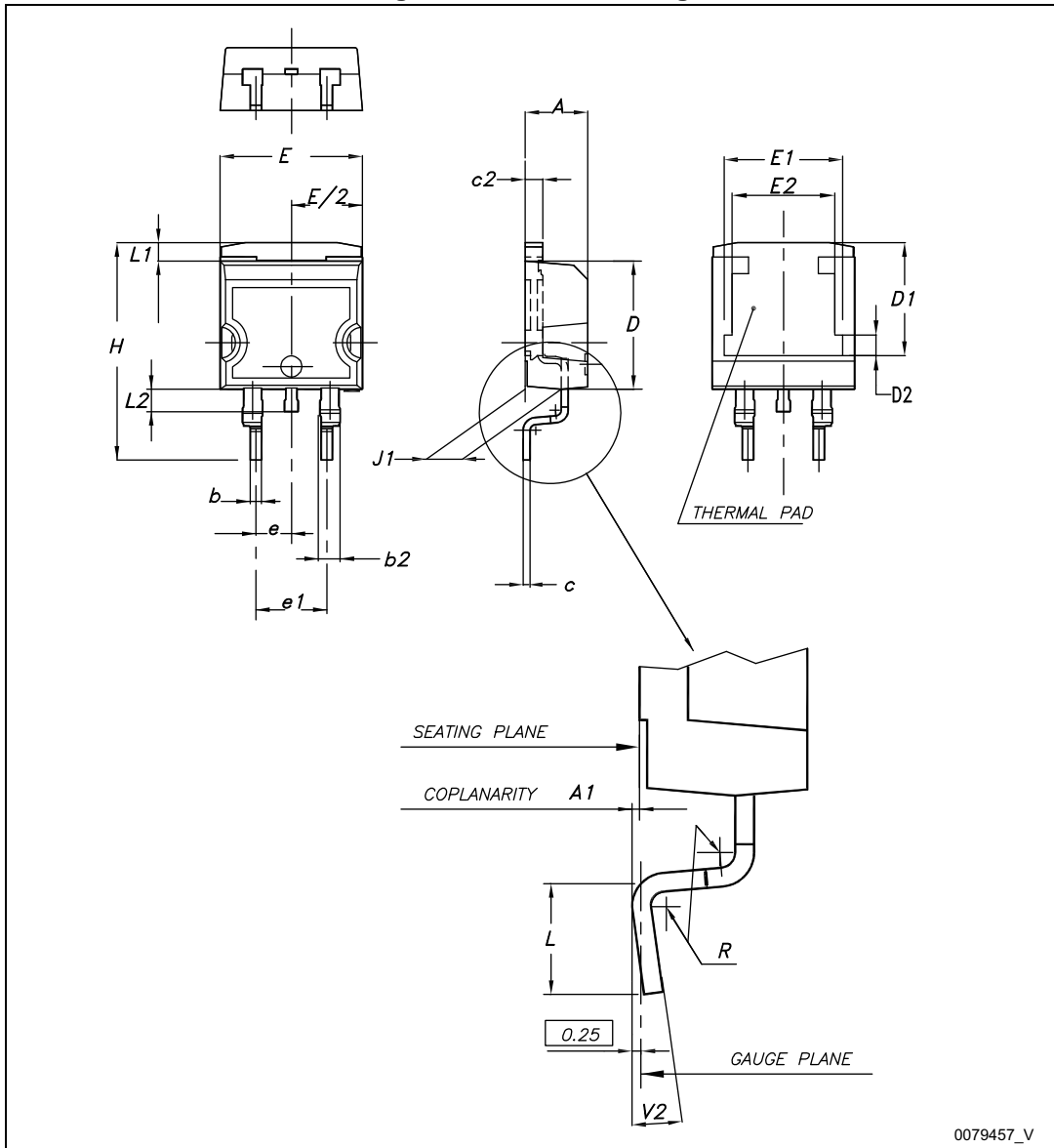
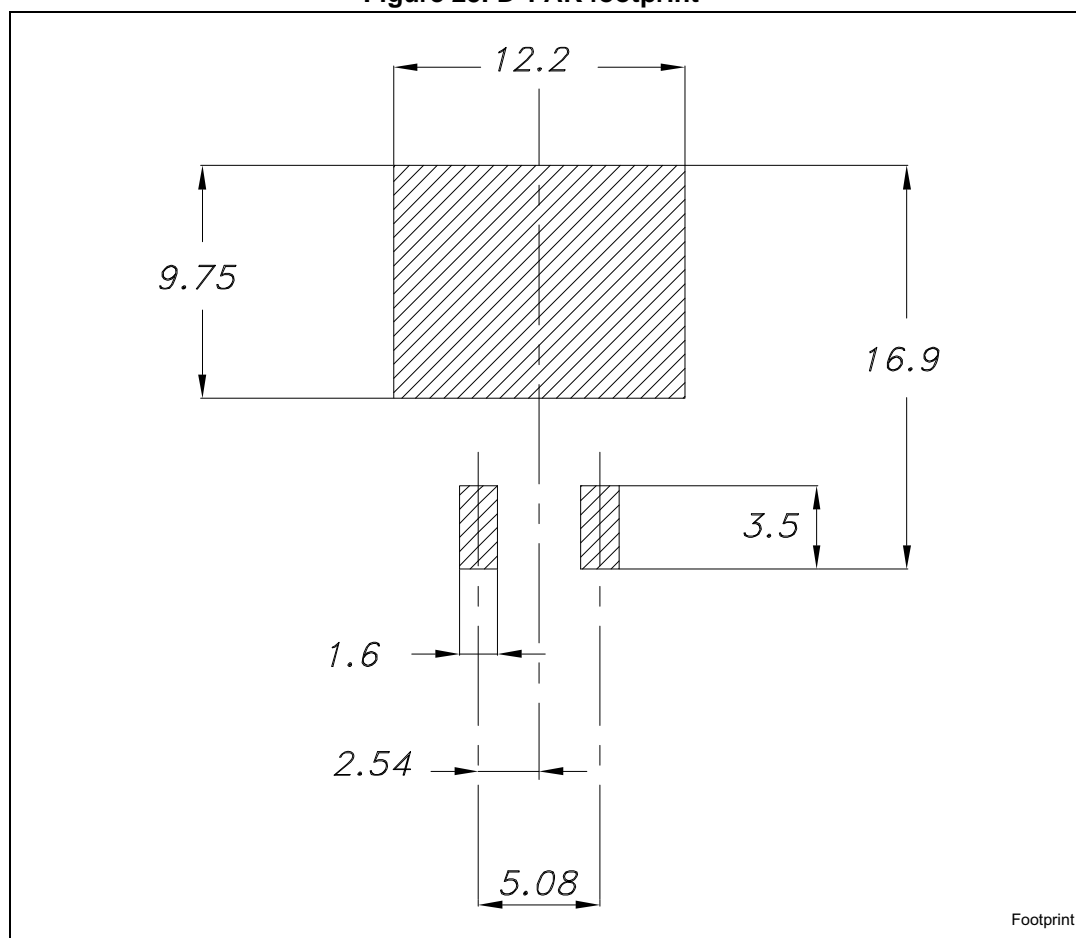


Table 9. D<sup>2</sup>PAK mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
A1	0.03		0.23
b	0.70		0.93
b2	1.14		1.70
c	0.45		0.60
c2	1.23		1.36
D	8.95		9.35
D1	7.50	7.75	8.00
D2	1.10	1.30	1.50
E	10		10.40
E1	8.50	8.70	8.90
E2	6.85	7.05	7.25
e		2.54	
e1	4.88		5.28
H	15		15.85
J1	2.49		2.69
L	2.29		2.79
L1	1.27		1.40
L2	1.30		1.75
R		0.4	
V2	0°		8°

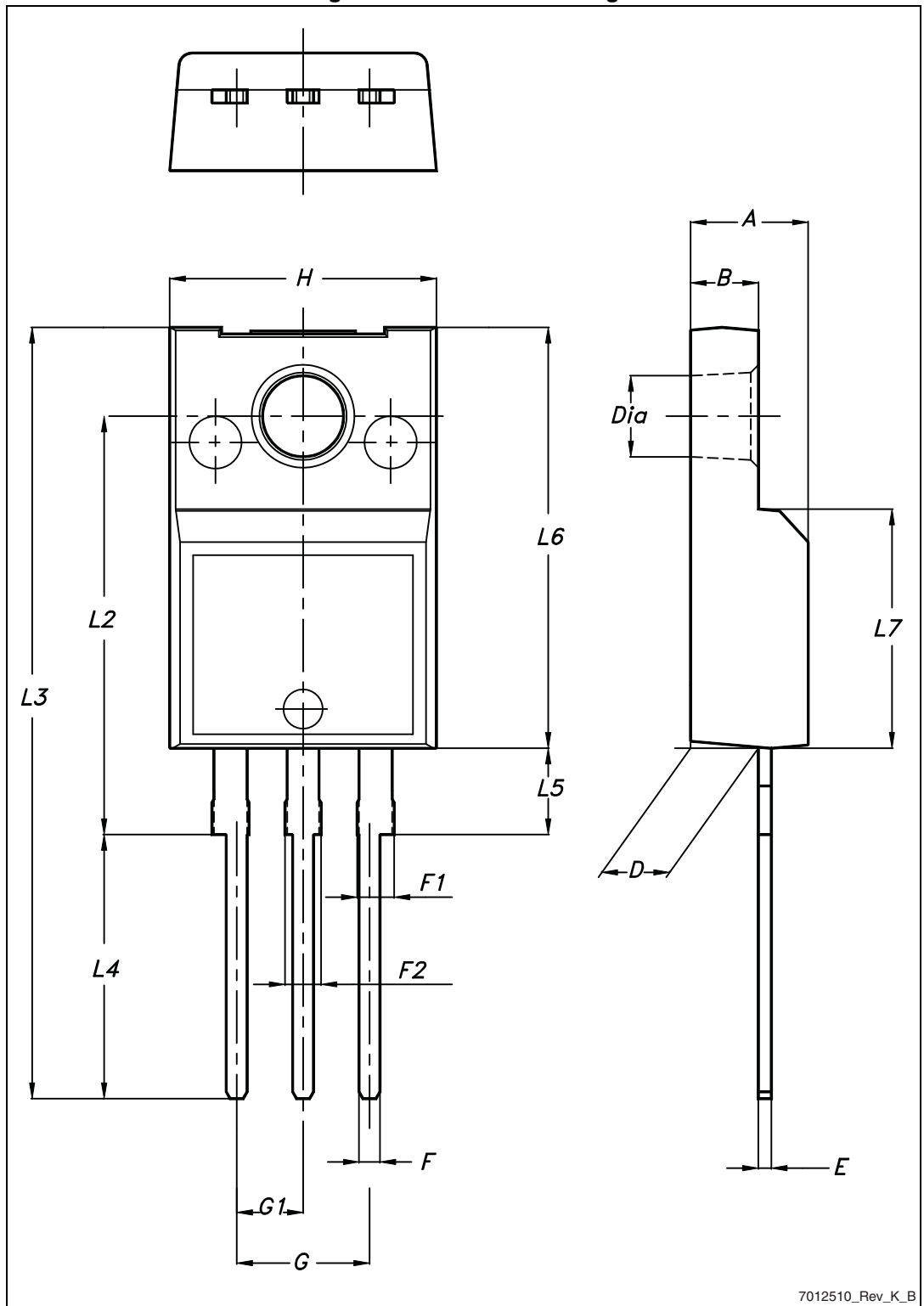
Figure 25. D<sup>2</sup>PAK footprint (a)



a. All dimensions are in millimeters

### 4.2 TO-220FP, STF28N65M2

Figure 26. TO-220FP drawing



7012510\_Rev\_K\_B

Table 10. TO-220FP mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.4		4.6
B	2.5		2.7
D	2.5		2.75
E	0.45		0.7
F	0.75		1
F1	1.15		1.70
F2	1.15		1.70
G	4.95		5.2
G1	2.4		2.7
H	10		10.4
L2		16	
L3	28.6		30.6
L4	9.8		10.6
L5	2.9		3.6
L6	15.9		16.4
L7	9		9.3
Ø	3		3.2

4.3 TO-220, STP28N65M2

Figure 27. TO-220 type A drawing

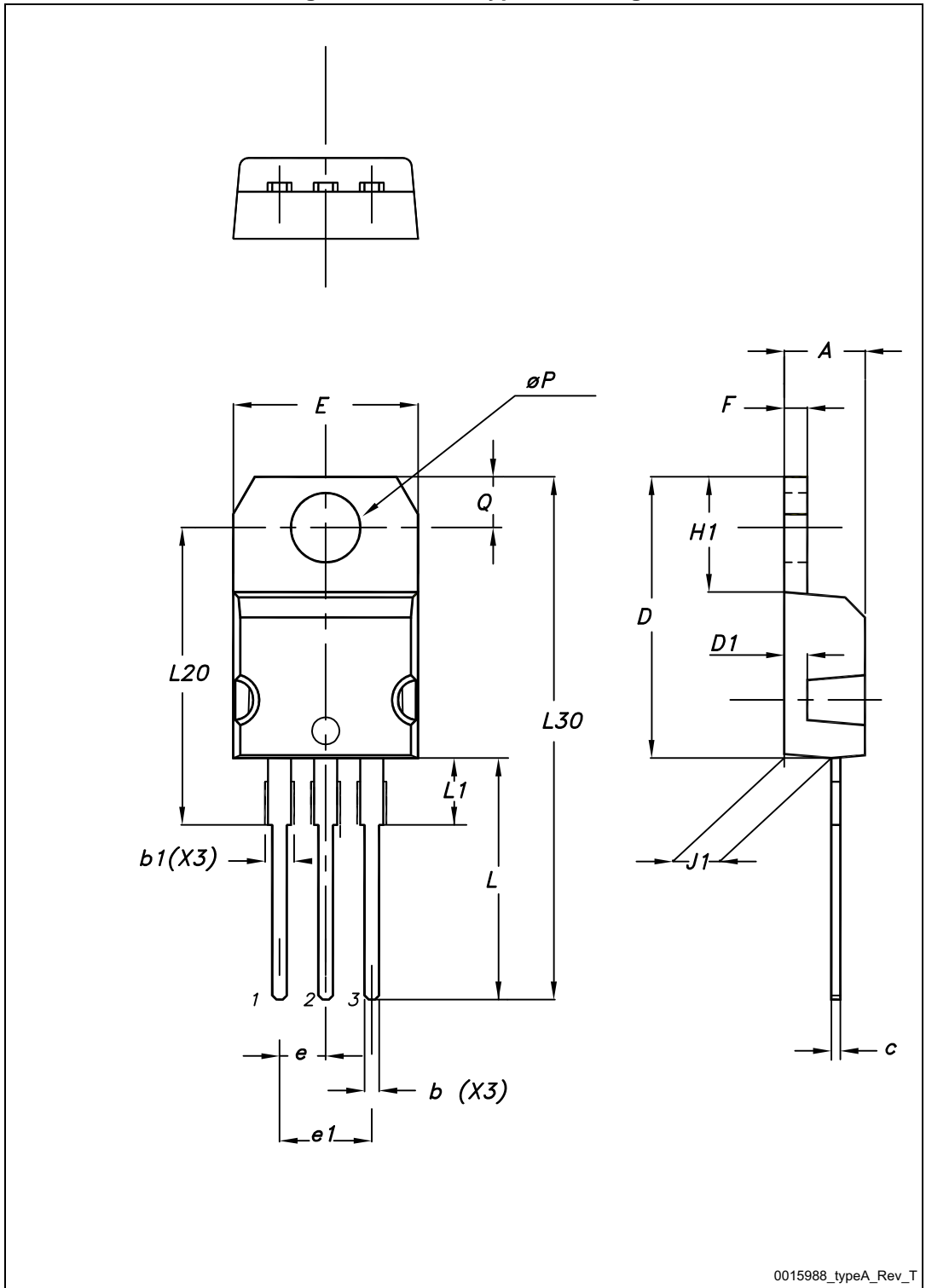


Table 11. TO-220 type A mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
b	0.61		0.88
b1	1.14		1.70
c	0.48		0.70
D	15.25		15.75
D1		1.27	
E	10		10.40
e	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13		14
L1	3.50		3.93
L20		16.40	
L30		28.90	
ØP	3.75		3.85
Q	2.65		2.95



### 4.4 TO-247, STW28N65M2

Figure 28. TO-247 drawing

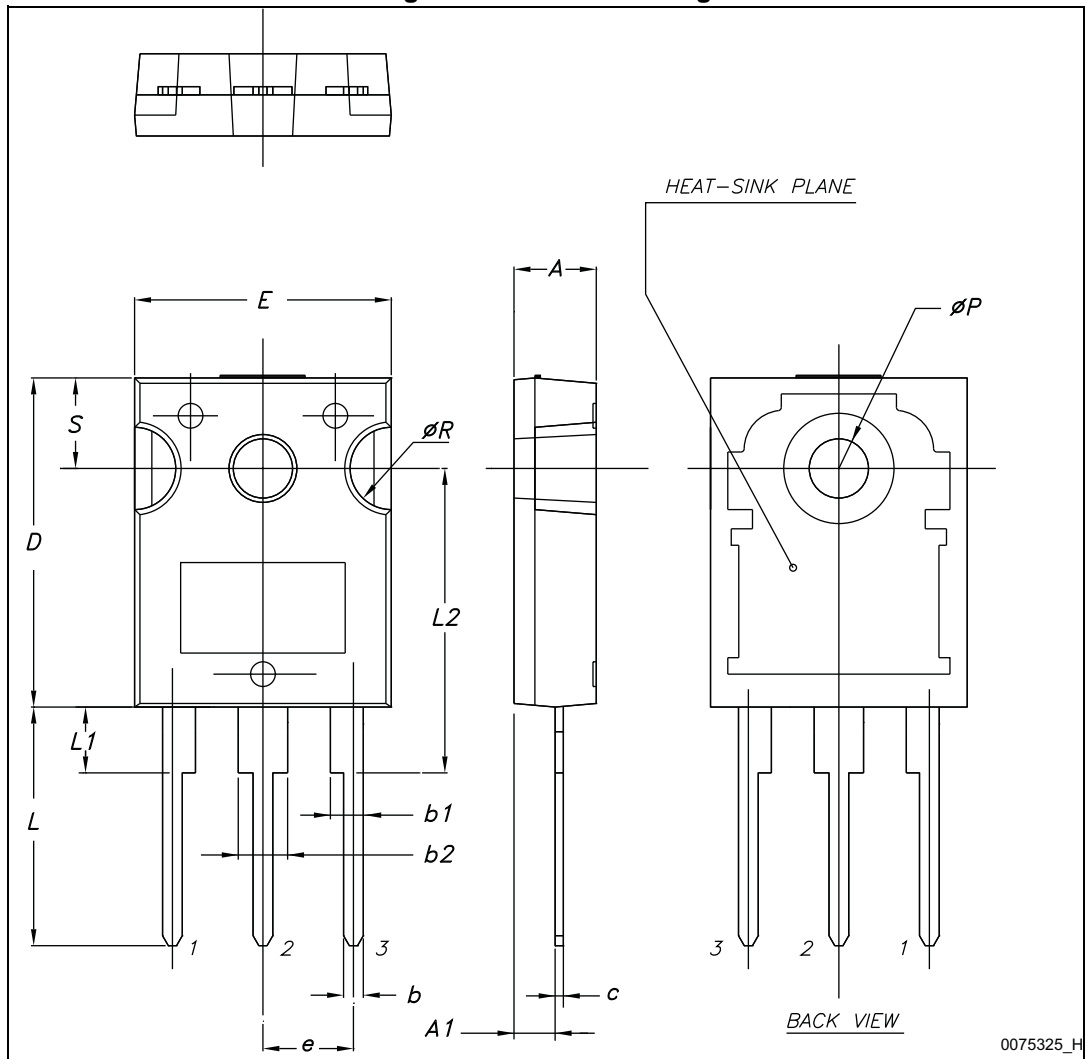


Table 12. TO-247 mechanical data

Dim.	mm.		
	Min.	Typ.	Max.
A	4.85		5.15
A1	2.20		2.60
b	1.0		1.40
b1	2.0		2.40
b2	3.0		3.40
c	0.40		0.80
D	19.85		20.15
E	15.45		15.75
e	5.30	5.45	5.60
L	14.20		14.80
L1	3.70		4.30
L2		18.50	
ØP	3.55		3.65
ØR	4.50		5.50
S	5.30	5.50	5.70

## 5 Packing mechanical data

Figure 29. Tape for D<sup>2</sup>PAK

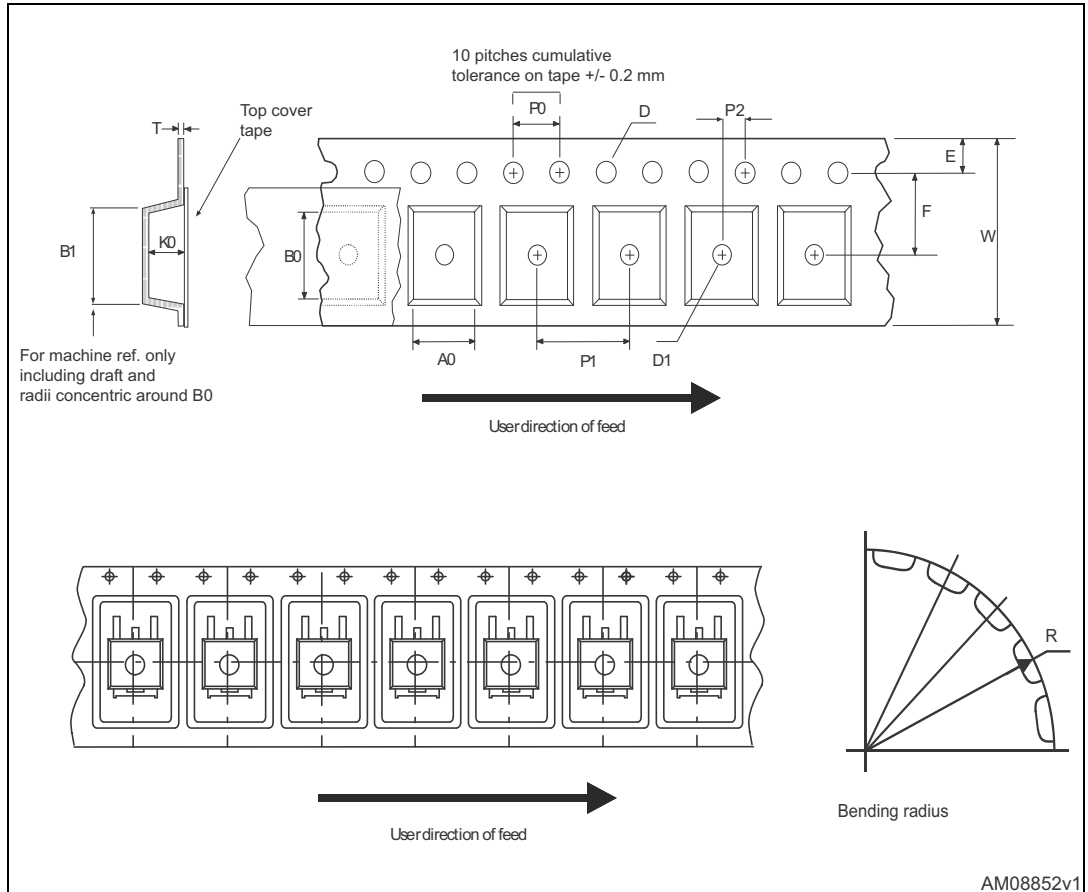


Figure 30. Reel for D<sup>2</sup>PAK

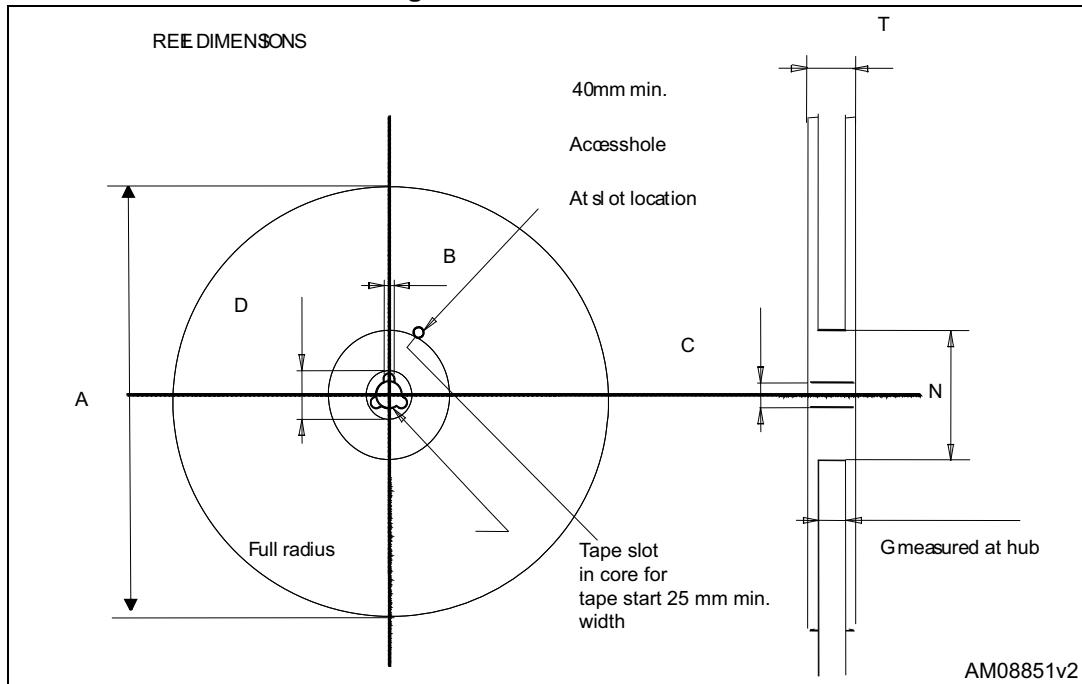


Table 13. D<sup>2</sup>PAK tape and reel mechanical data

Tape			Reel		
Dim.	mm		Dim.	mm	
	Min.	Max.		Min.	Max.
A0	10.5	10.7	A		330
B0	15.7	15.9	B	1.5	
D	1.5	1.6	C	12.8	13.2
D1	1.59	1.61	D	20.2	
E	1.65	1.85	G	24.4	26.4
F	11.4	11.6	N	100	
K0	4.8	5.0	T		30.4
P0	3.9	4.1			
P1	11.9	12.1		Base qty	1000
P2	1.9	2.1		Bulk qty	1000
R	50				
T	0.25	0.35			
W	23.7	24.3			

## 6 Revision history

Table 14. Document revision history

Date	Revision	Changes
09-Dec-2014	1	First release.

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